



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

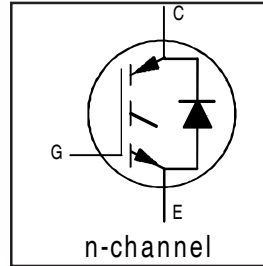


# IRG4PC50UDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE UltraFast CoPack IGBT

## Features

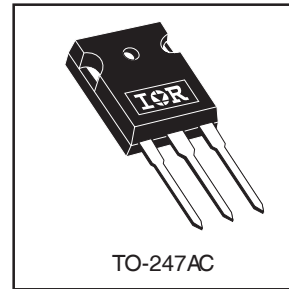
- UltraFast: Optimized for high operating frequencies 8-40 kHz in hard switching, >200 kHz in resonant mode
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-247AC package
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 1.65V$
@ $V_{GE} = 15V, I_C = 27A$

## Benefits

- Generation 4 IGBT's offer highest efficiencies available
- IGBT's optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBT's. Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBT's



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	55	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	27	
$I_{CM}$	Pulsed Collector Current ①	220	
$I_{LM}$	Clamped Inductive Load Current ②	220	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	25	
$I_{FM}$	Diode Maximum Forward Current	220	W
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

## Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	-----	-----	0.64	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	-----	-----	0.83	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	-----	0.24	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	40	
Wt	Weight	-----	6 (0.21)	-----	g (oz)

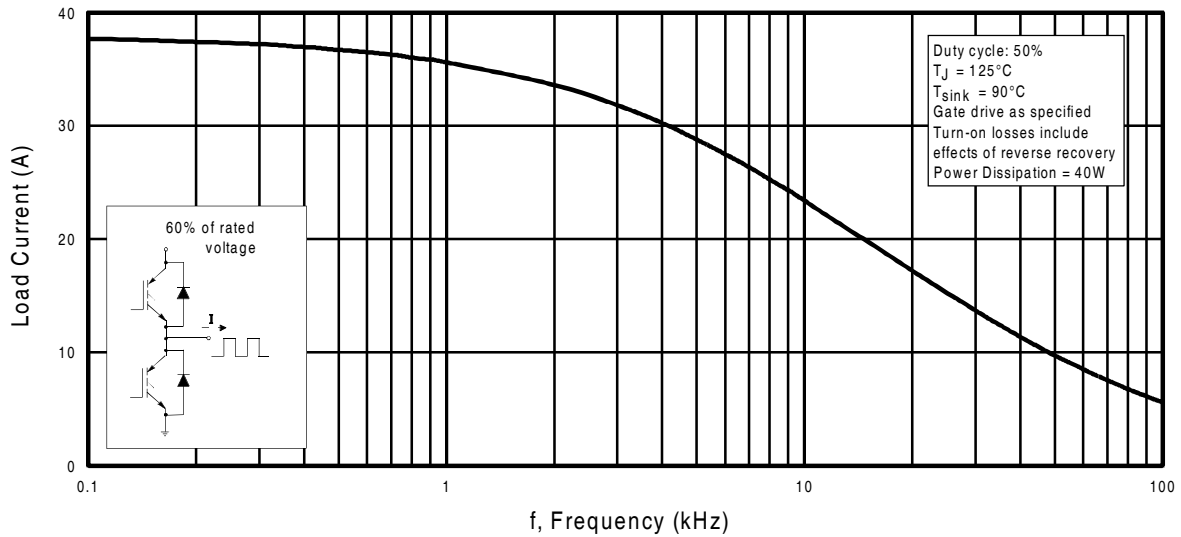
# IRG4PC50UDPbF

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

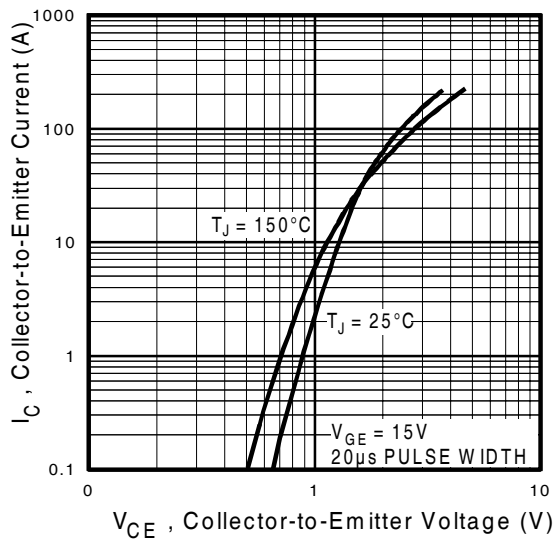
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	600	----	----	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	----	0.60	----	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	----	1.65	2.0	V	$I_C = 27A$ $I_C = 55A$ $I_C = 27A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig. 2, 5
		----	2.0	----		
		----	1.6	----		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	----	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	----	-13	----	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance <sup>④</sup>	16	24	----	S	$V_{CE} = 100V, I_C = 27A$
$I_{CES}$	Zero Gate Voltage Collector Current	----	----	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$
		----	----	6500		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$V_{FM}$	Diode Forward Voltage Drop	----	1.3	1.7	V	$I_C = 25A$ See Fig. 13
		----	1.2	1.5		$I_C = 25A, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	----	----	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

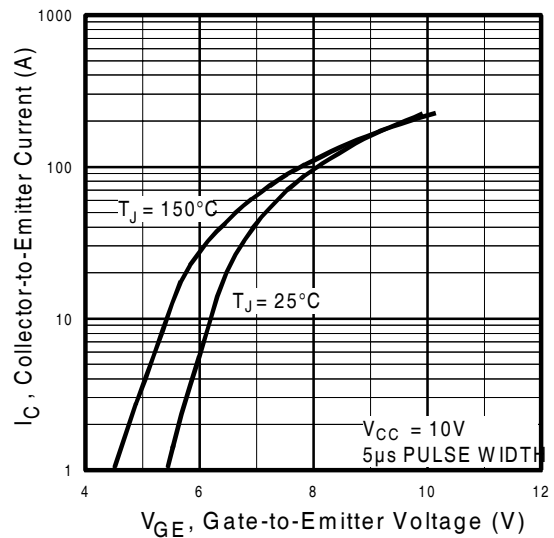
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	----	180	270		$I_C = 27A$
$Q_{ge}$	Gate - Emitter Charge (turn-on)	----	25	38	nC	$V_{CC} = 400V$ See Fig. 8
$Q_{gc}$	Gate - Collector Charge (turn-on)	----	61	90		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	----	46	----		$T_J = 25^\circ\text{C}$
$t_r$	Rise Time	----	25	----	ns	$I_C = 27A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	----	140	230		$V_{GE} = 15V, R_G = 5.0\Omega$
$t_f$	Fall Time	----	74	110		Energy losses include "tail" and diode reverse recovery.
$E_{on}$	Turn-On Switching Loss	----	0.99	----		See Fig. 9, 10, 11, 18
$E_{off}$	Turn-Off Switching Loss	----	0.59	----	mJ	
$E_{is}$	Total Switching Loss	----	1.58	1.9		
$t_{d(on)}$	Turn-On Delay Time	----	44	----		$T_J = 150^\circ\text{C}$ , See Fig. 9, 10, 11, 18
$t_r$	Rise Time	----	27	----	ns	$I_C = 27A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	----	240	----		$V_{GE} = 15V, R_G = 5.0\Omega$
$t_f$	Fall Time	----	130	----		Energy losses include "tail" and diode reverse recovery.
$E_{is}$	Total Switching Loss	----	2.3	----	mJ	Measured 5mm from package
$L_E$	Internal Emitter Inductance	----	13	----	nH	$V_{GE} = 0V$
$C_{ies}$	Input Capacitance	----	4000	----		
$C_{oes}$	Output Capacitance	----	250	----	pF	$V_{CC} = 30V$ See Fig. 7
$C_{res}$	Reverse Transfer Capacitance	----	52	----		$f = 1.0MHz$
$t_{rr}$	Diode Reverse Recovery Time	----	50	75	ns	$T_J = 25^\circ\text{C}$ See Fig.
		----	105	160		$T_J = 125^\circ\text{C}$ 14 $I_F = 25A$
$I_{rr}$	Diode Peak Reverse Recovery Current	----	4.5	10	A	$T_J = 25^\circ\text{C}$ See Fig.
		----	8.0	15		$T_J = 125^\circ\text{C}$ 15
$Q_{rr}$	Diode Reverse Recovery Charge	----	112	375	nC	$T_J = 25^\circ\text{C}$ See Fig.
		----	420	1200		$T_J = 125^\circ\text{C}$ 16
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During $t_b$	----	250	----	A/ $\mu s$	$T_J = 25^\circ\text{C}$
		----	160	----		$T_J = 125^\circ\text{C}$
						$V_R = 200V$ $di/dt 200A/\mu s$



**Fig. 1 - Typical Load Current vs. Frequency**  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

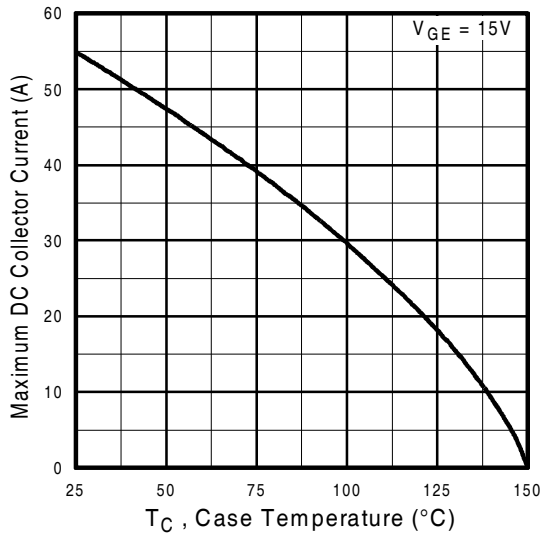


**Fig. 2 - Typical Output Characteristics**

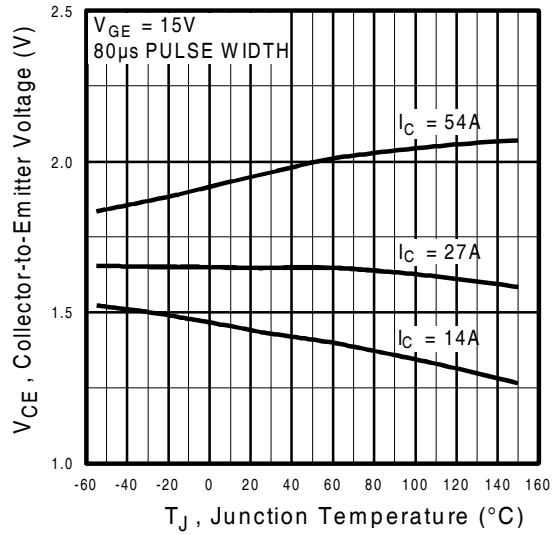


**Fig. 3 - Typical Transfer Characteristics**

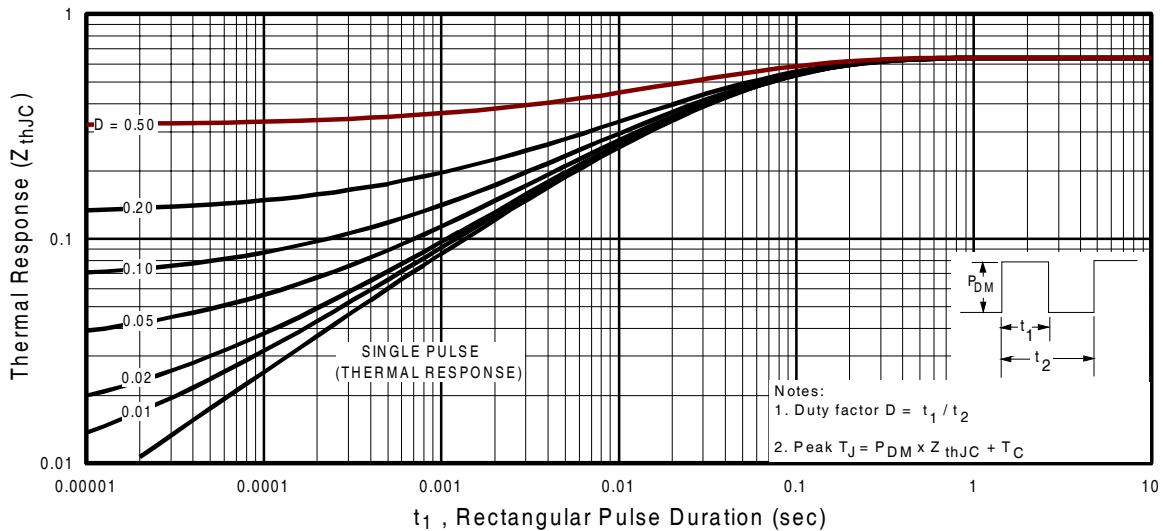
# IRG4PC50UDPbF



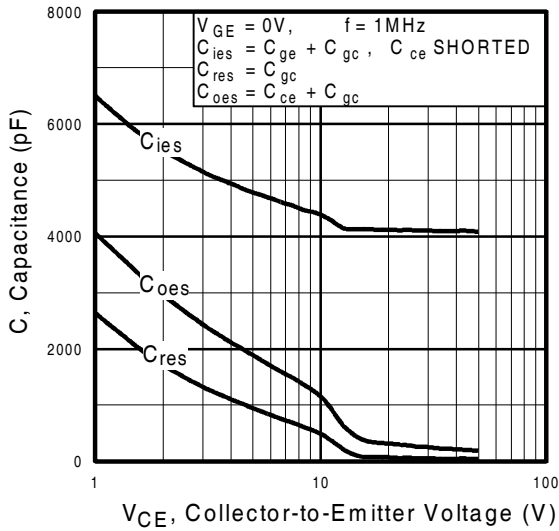
**Fig. 4** - Maximum Collector Current vs. Case Temperature



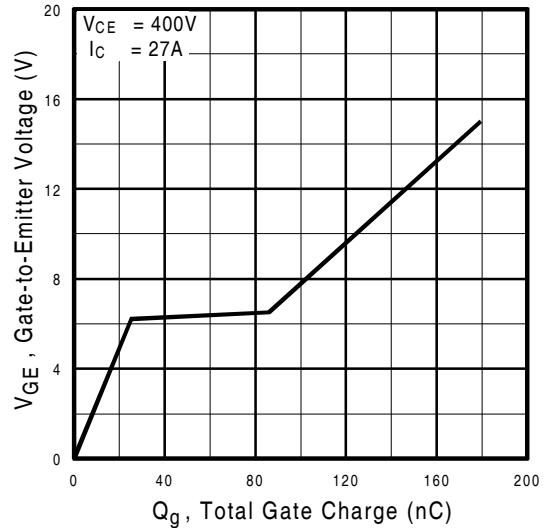
**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature



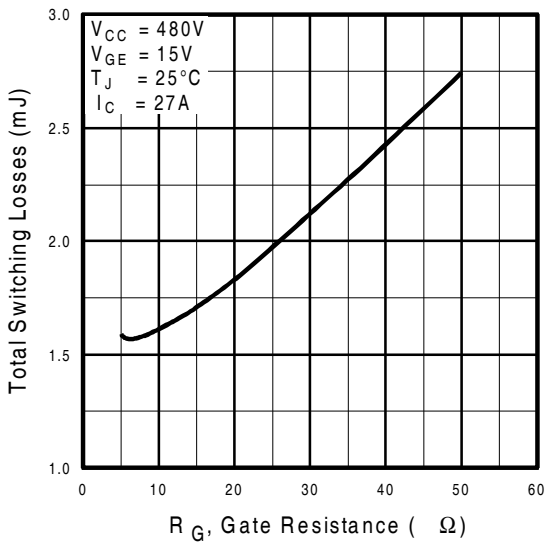
**Fig. 6** - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case



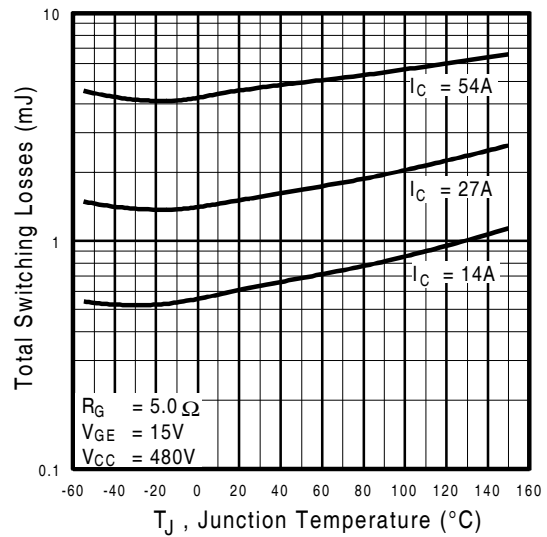
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

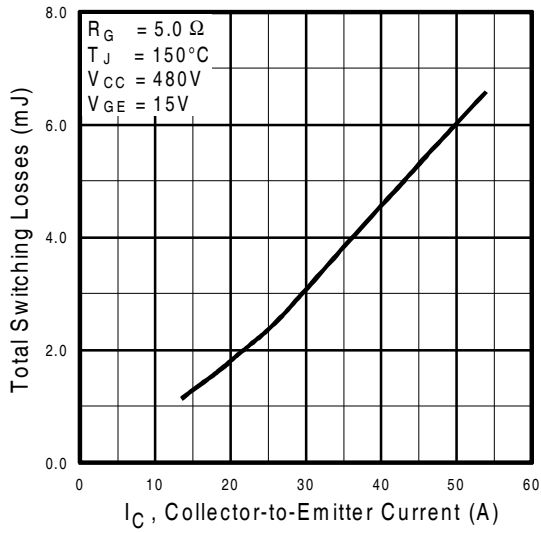


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

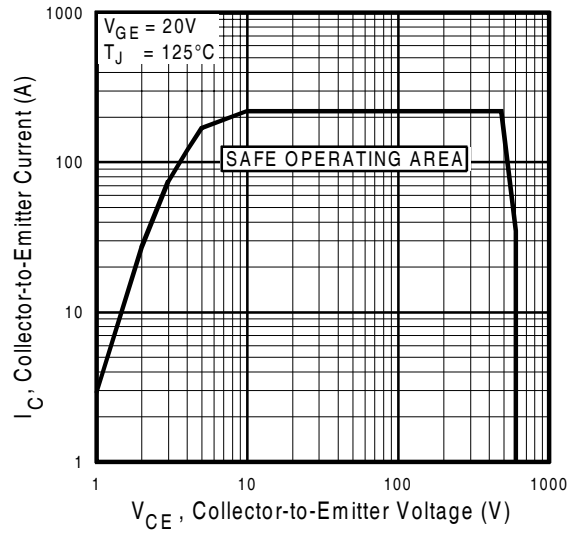


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

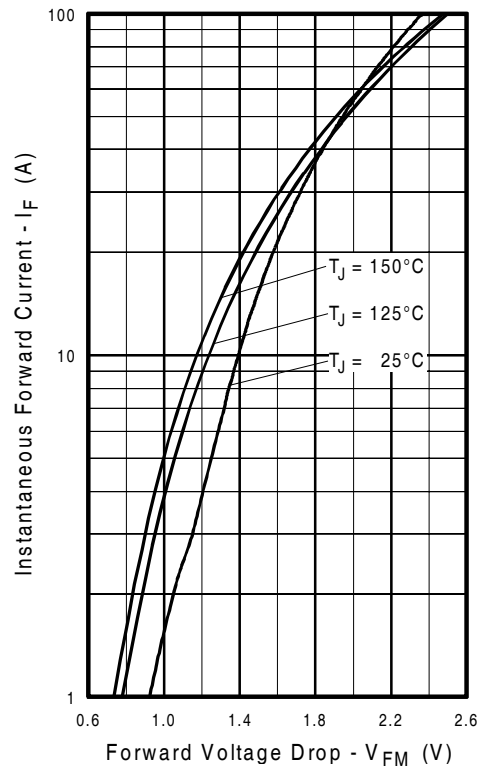
# IRG4PC50UDPbF



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



**Fig. 12** - Turn-Off SOA



**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

# IRG4PC50UDPbF

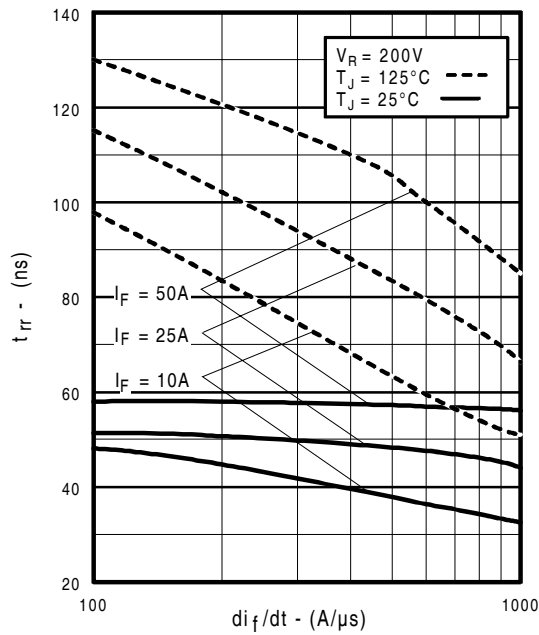


Fig. 14 - Typical Reverse Recovery vs.  $di_f/dt$

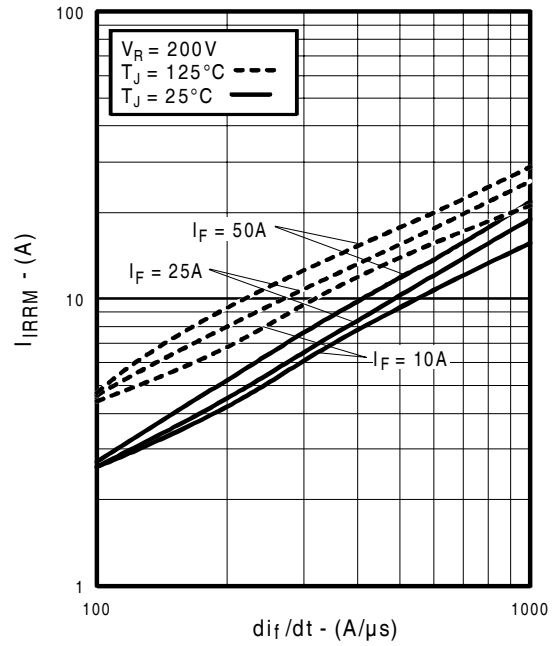


Fig. 15 - Typical Recovery Current vs.  $di_f/dt$

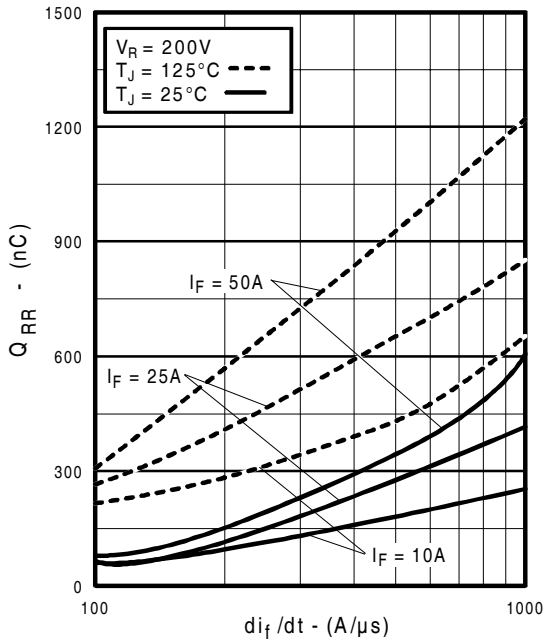


Fig. 16 - Typical Stored Charge vs.  $di_f/dt$

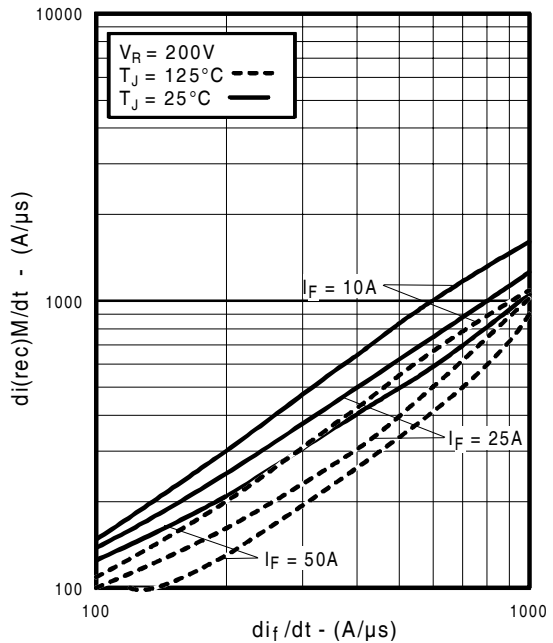
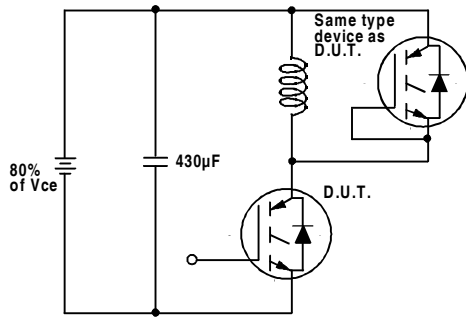


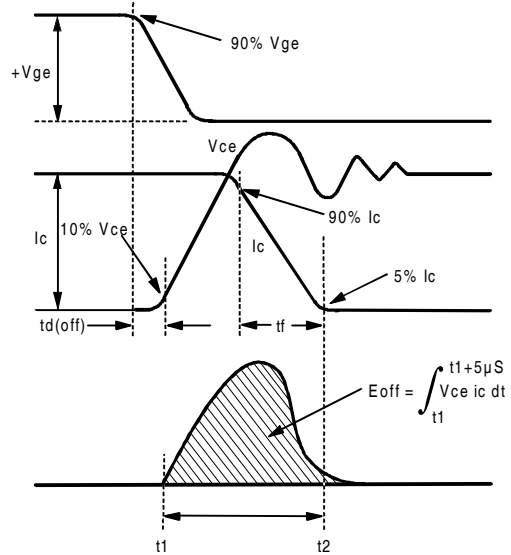
Fig. 17 - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$



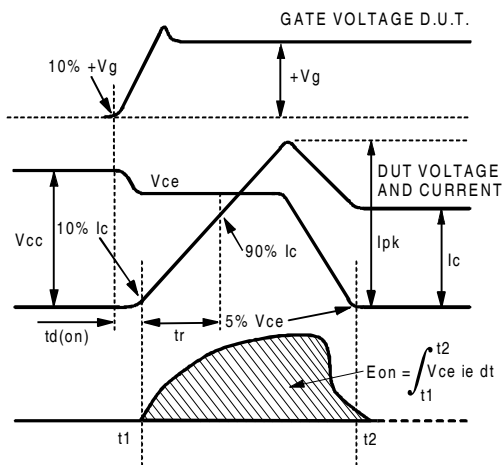
# IRG4PC50UDPbF



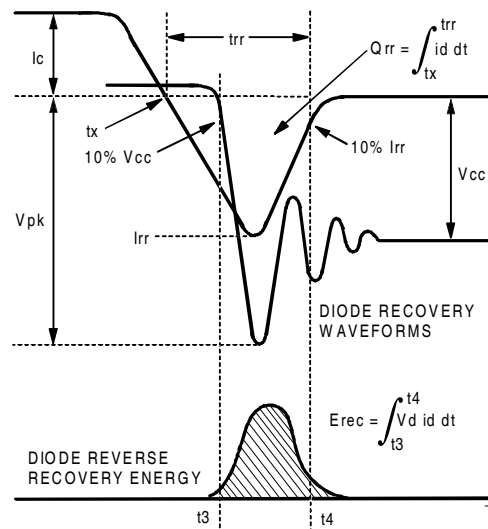
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$

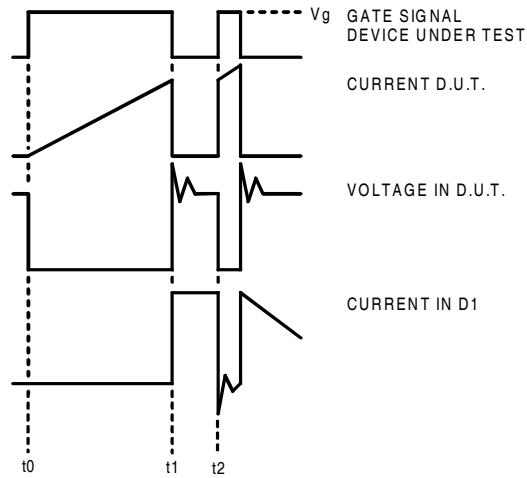


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

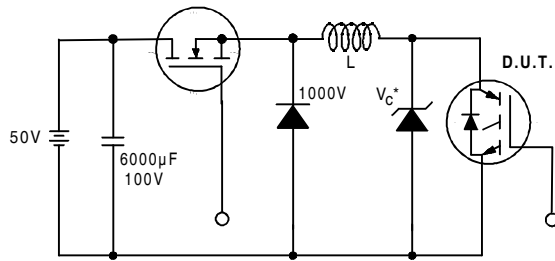


Figure 19. Clamped Inductive Load Test Circuit

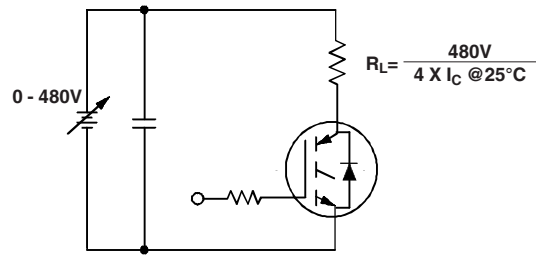


Figure 20. Pulsed Collector Current Test Circuit

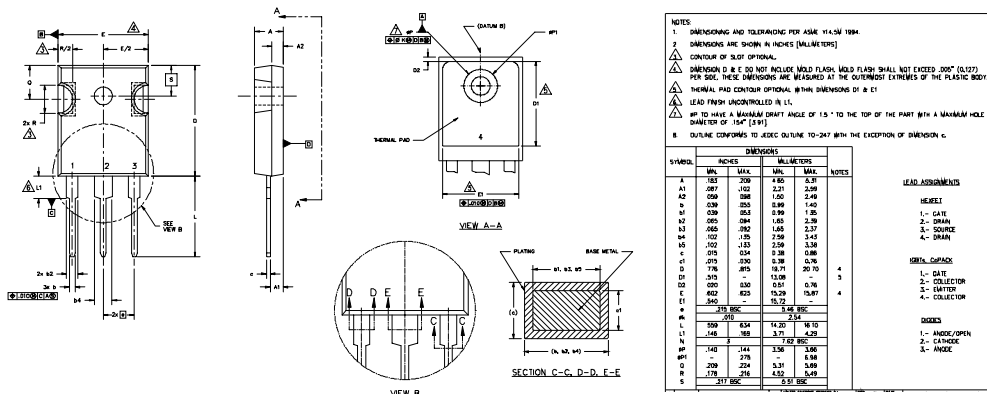
# IRG4PC50UDPbF

## Notes:

- ① Repetitive rating:  $V_{GE} = 20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC} = 80\%(V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 10\mu H$ ,  $R_G = 5.0\Omega$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.

## TO-247AC Package Outline

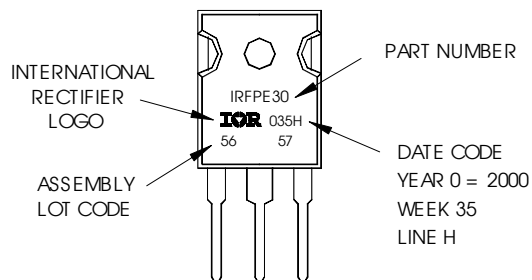
Dimensions are shown in millimeters (inches)



## TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30  
WITH ASSEMBLY  
LOT CODE 5657  
ASSEMBLED ON WW 35, 2000  
IN THE ASSEMBLY LINE "H"

**Note:** "P" in assembly line  
position indicates "Lead-Free"



Data and specifications subject to change without notice.

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>